

Title (en)
DRUM TYPE WASHING MACHINE AND DRYING METHOD THEREOF

Title (de)
TROMMELWASCHMASCHINE UND DAZUGEHÖRIGES TROCKNUNGSVERFAHREN

Title (fr)
MACHINE À LAVER À TAMBOUR ET PROCÉDÉ DE SÉCHAGE ASSOCIÉ

Publication
EP 2007941 A4 20100526 (EN)

Application
EP 07708732 A 20070202

Priority
• KR 2007000581 W 20070202
• KR 20060027154 A 20060324

Abstract (en)
[origin: US2007220683A1] A nonvolatile semiconductor memory device which is superior in writing and charge holding properties, including a semiconductor substrate in which a channel formation region is formed between a pair of impurity regions formed with an interval, and a first insulating layer, a floating gate, a second insulating layer, and a control gate over an upper layer portion of the semiconductor substrate. It is preferable that a band gap of a semiconductor material forming the floating gate be smaller than that of the semiconductor substrate. For example, it is preferable that the band gap of the semiconductor material forming the floating gate be smaller than that of the channel formation region in the semiconductor substrate by 0.1 eV or more. This is because, by decreasing the bottom energy level of a conduction band of the floating gate electrode to be lower than that of the channel formation region in the semiconductor substrate, carrier injecting and charge holding properties are improved.

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D06F 58/28 (2006.01)

CPC (source: EP KR US)
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Citation (search report)
• [XAI] EP 1508637 A2 20050223 - LG ELECTRONICS INC [KR]
• [A] US 6373032 B1 20020416 - BRUNTZ JORDAN S [US], et al
• [A] EP 1544342 A2 20050622 - LG ELECTRONICS INC [KR]
• See references of WO 2007111413A1

Designated contracting state (EPC)
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DOCDB simple family (publication)
US 2007220683 A1 20070927; CN 101410565 A 20090415; EP 2007941 A1 20081231; EP 2007941 A4 20100526; JP 2009531124 A 20090903; KR 100692582 B1 20070314; WO 2007111413 A1 20071004

DOCDB simple family (application)
US 72347507 A 20070320; CN 200780010547 A 20070202; EP 07708732 A 20070202; JP 2009502655 A 20070202; KR 20060027154 A 20060324; KR 2007000581 W 20070202